

CSE 350

Digital Electronics and Pulse Techniques

Lab Report

Experiment No: 02

Implementing Diode Logic (DL) gates

Submitted by:

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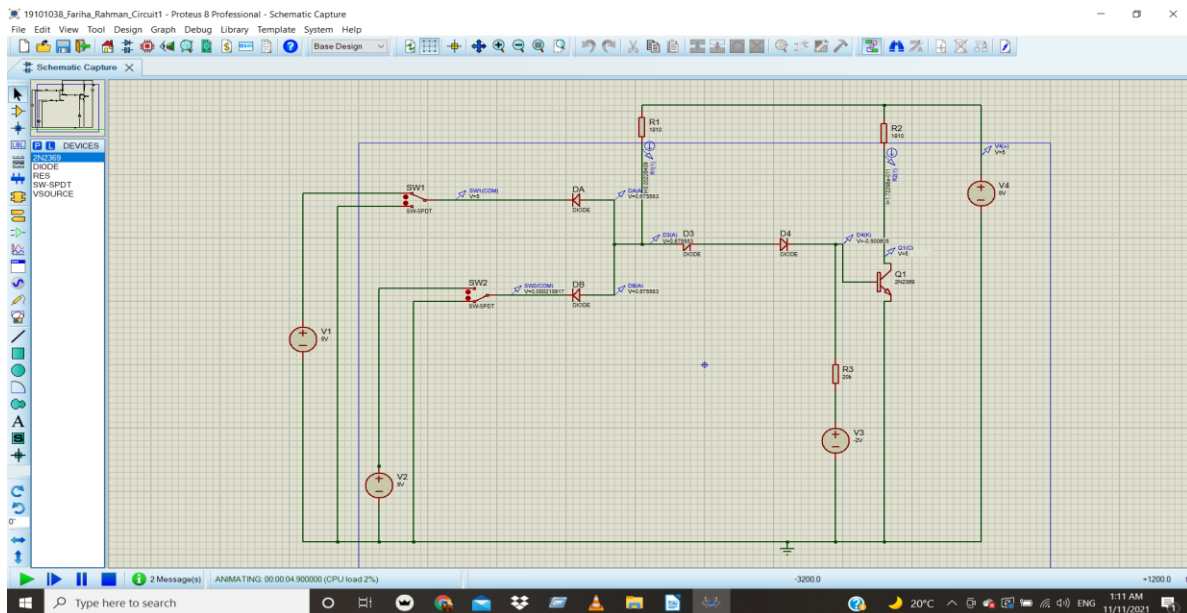
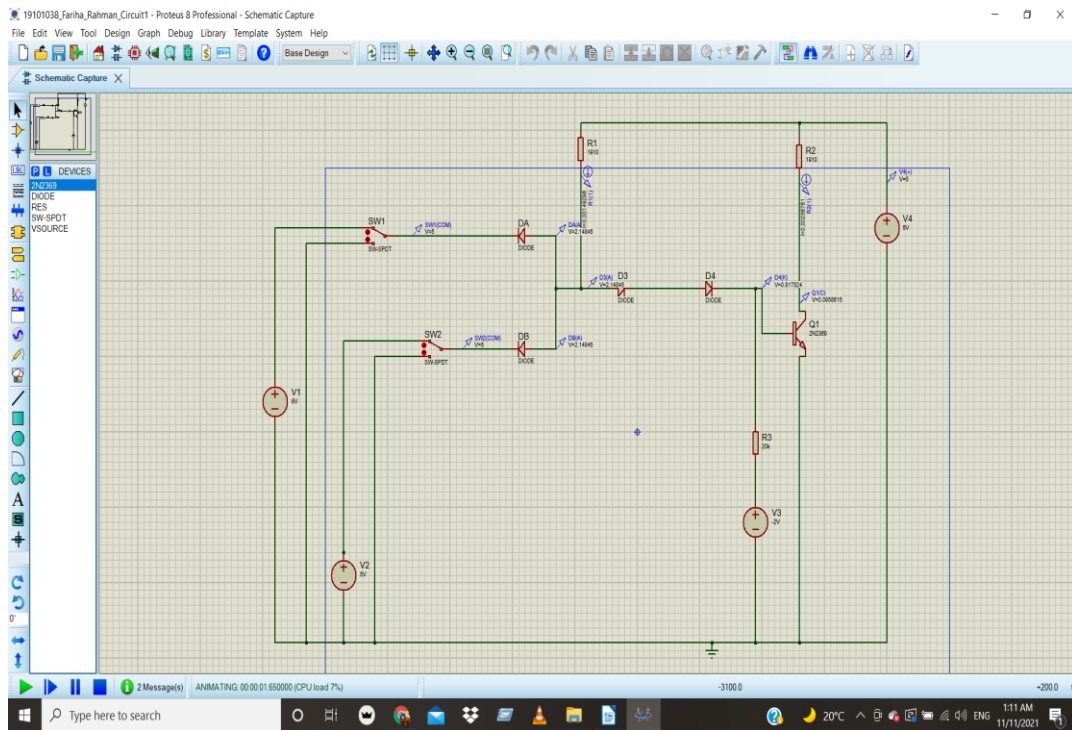
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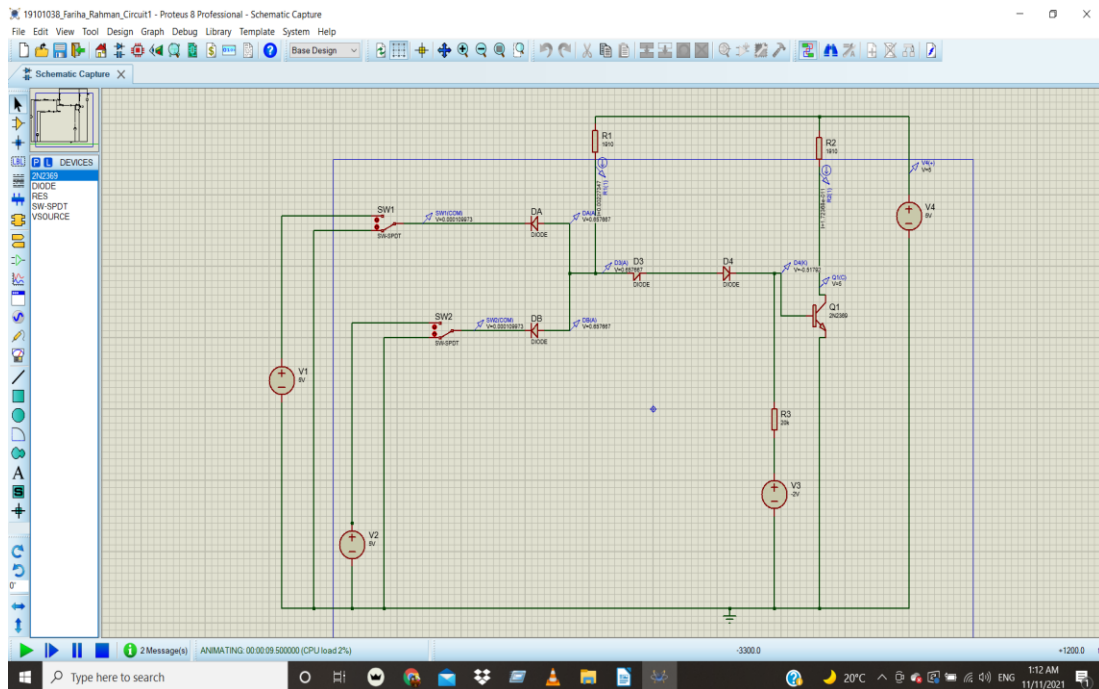
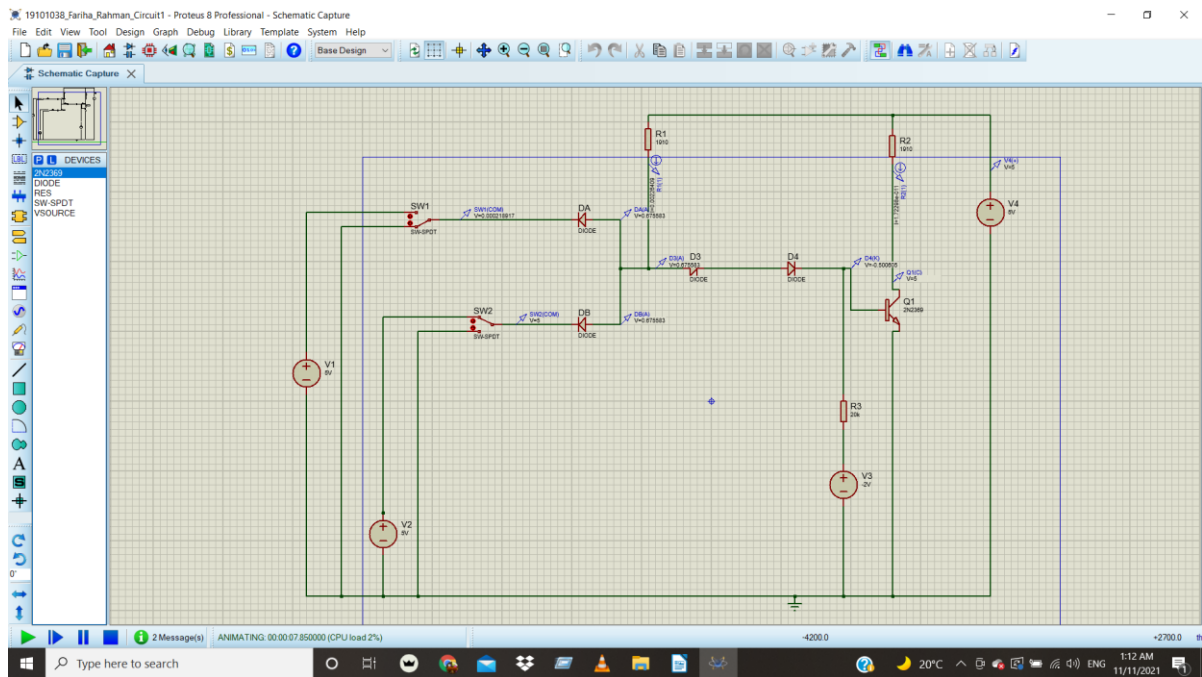
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NAND Gate (Table 1)

Input A	Input B	V_{OA}	V_{OB}	V_P	V_{R1}	I_{R2}	V_b	y
0	0	0.657	0.657	0.657	0.02	1.72×10^{-11}	0.517	5
0	1	0.657	4.33	0.675	0.02	1.72×10^{-11}	0.5	5
1	0	4.33	0.675	0.675	0.02	1.72×10^{-11}	0.5	5
1	1	2.851	2.851	2.148	0.001	0.002	0.817	0.95

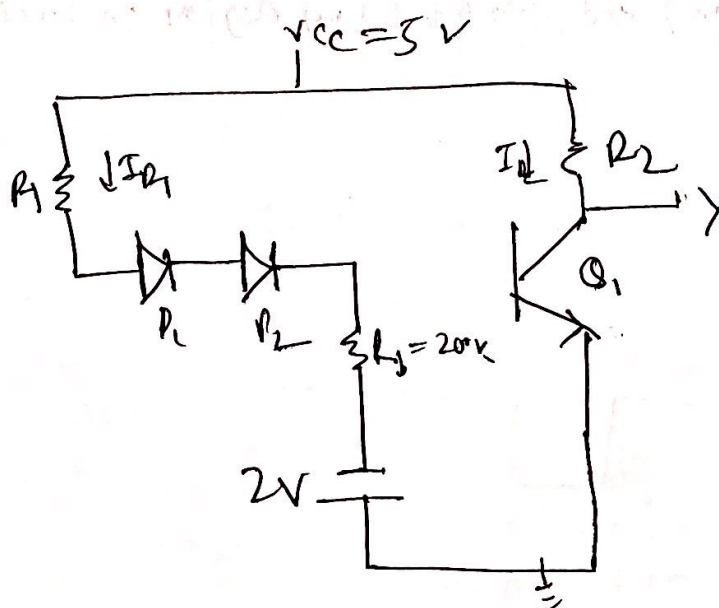
NAND Gate As Inverter (Table 2)

Input A	Input B	V_P	V_b	y
1	0	0.675	0.5	5
1	1	2.148	0.817	0.95

Report

Answer to the Question No-1

When both of the inputs of the circuit are HIGH then the active part is shown below—



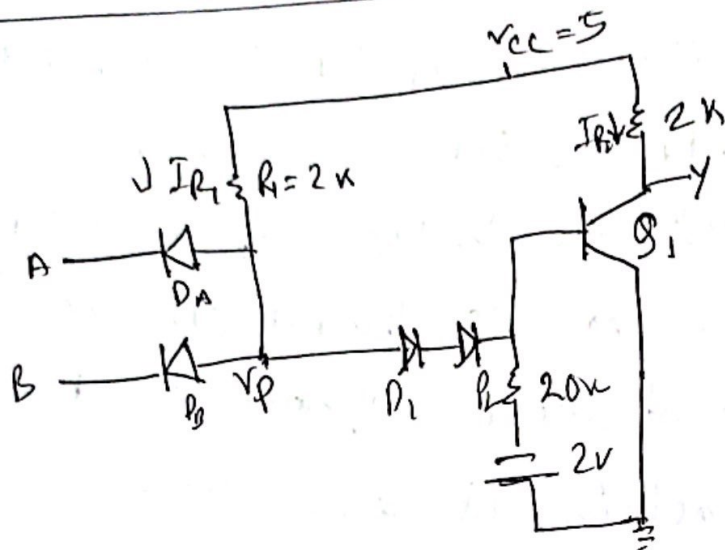
Ans to the Question No 2

In Table 2, when we set Input A = HIGH and when Input B is LOW, D_A was OFF and diode D_B was turned ON. So, at p node the voltage, V_p was approximately 0.7 V. As we know to turn on the Q_1 transistor we have to drive at least 2.1 volt at p node. But, we did not achieve it in this case. which conclude Q_1 was in Cut off mode and we get 5 / HIGH in the output.

Also, when Input B = HIGH, diode D_A , D_B will be off. So, V_p will be approximately 2.1 V. That means the transistor is in Saturation mode. When transistor is in saturation mode we get 0.1 / 0.2 V from the collector-emitter junction (close to 0). So, we get 0 / Low from output. This is why

~~As Inverter can be used as~~
NAND gate can be used as an Inverter.

Answer to the Question - 3



When the both inputs are low / 0 volt, D_A, D_B will be ON. So, V_P will be approximately $0.7V$ which is less than $(0.8 + 0.7 + 0.7)V = 2.2V$.

$0.8V$ is base emitter voltage. $0.7V$ is conducting voltage for diode. So, Q_1 will be in Cut off mode. So, no current will pass and the output will be High / $5V$.

: When any of the input is high. Let's consider, $A = \text{High}$ and $B = \text{Low}$. So, $D_A = \text{OFF}, D_B = \text{ON}$.

So, $V_P \sim 0.7V$ which is ~~less~~ less than $2.2V$.

So, we can say that Q_1 will be in Cut off mode.

So, No current will pass and the output will be High / $5V$.

Same will happen when $A = \text{Low}$ and $B = \text{High}$

Therefore, when both ^{of} the inputs are high, then $D_A = D_B = \text{OFF}$. So, the I (current) will go through D_1 and D_2 diode ^{and} a Q1 transistor. So, Q_1 will be in Saturation Mode. So, $Q_1 \text{ output} = \text{Low}$.
 This is how NAND operations are performed.
Ans to the question No-4:

From proteus simulation, 1 of the input is high then, $V_B = -0.5 \text{ V}$. So, $V_B = -0.5 \text{ [VE = 0V]}$ and $V_C = 5 \text{ V}$. So, $V_E > V_B$ and $V_C > V_B$.

~~Agreed~~ So, Q_1 will be cutoff.

Ans. to the Question No-5

When one of the inputs one High which is 5 V . We get an output of 5 V which is High.
 So, the maximum input is 5 Volts .